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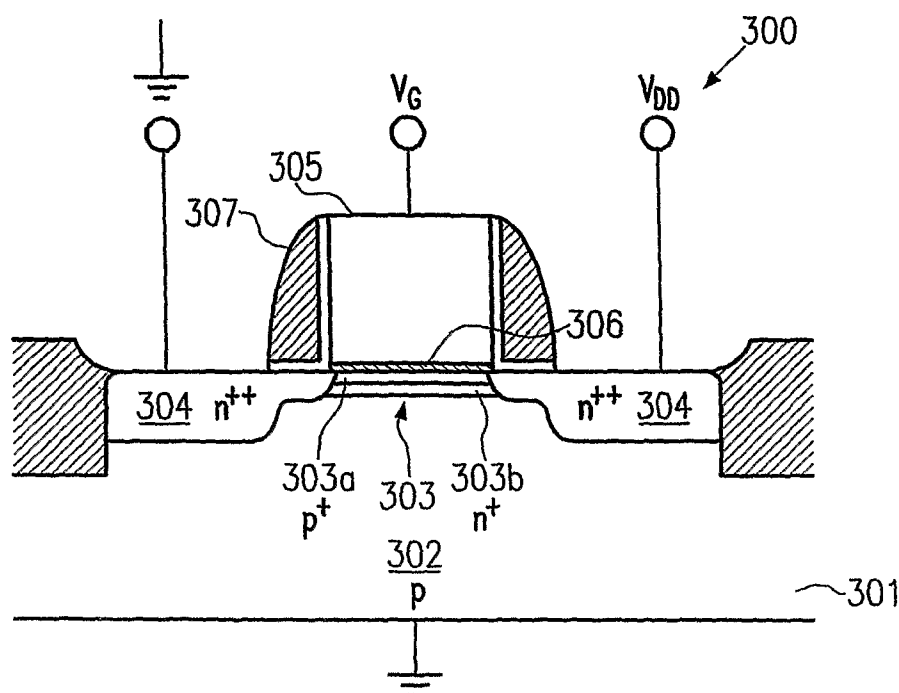
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(54) Title: SELF-BIASING TRANSISTOR STRUCTURE AND SRAM CELL



(57) Abstract: By providing a self-biasing semiconductor switch, an SRAM cell (450) having a reduced number of individual active components may be realized. In particular embodiments, the self-biasing semiconductor device may be provided in the form of a double channel field effect transistor (400) that allows the formation of an SRAM cell (450) with less than six transistor elements and, in preferred embodiments, with as few as two individual transistor elements.

WO 2006/022915 A1